

3918590 GENERAL SEMICONDUCTOR

95D 02083 D

T-11-15



**General Semiconductor Industries, Inc.**  
SQUARE D COMPANY

**ZENER DIODES  
5 WATTS AVERAGE**

**1N5333  
THRU  
1N5388**

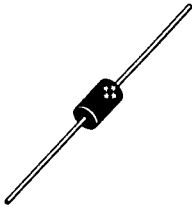
**FEATURES**

- Oxide Passivated Junctions
- Each device 100% tested

**DESCRIPTION**

This series of zener diodes is fully specified for use in high power regulator applications. These devices are particularly useful in situations where large surge currents are expected. The series has oxide passivated junctions and is packaged in a rugged transfer molded plastic package to offer excellent reliability in all commercial environments.

**CASE 7**



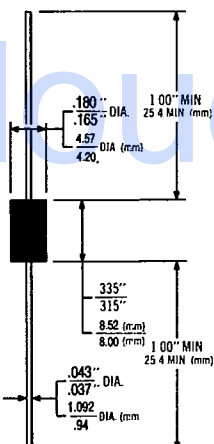
**MAXIMUM RATINGS**

- JUNCTION AND STORAGE TEMPERATURE: -65 to +200°C
- LEAD TEMPERATURE: Not less than 1/16" from the case for 10 seconds @ 230°C
- dc POWER DISSIPATION: 5.0W @ TL = 75°C, Lead Length = 3/8" (Derate 40mW/°C above 75°C)

**MECHANICAL CHARACTERISTICS**

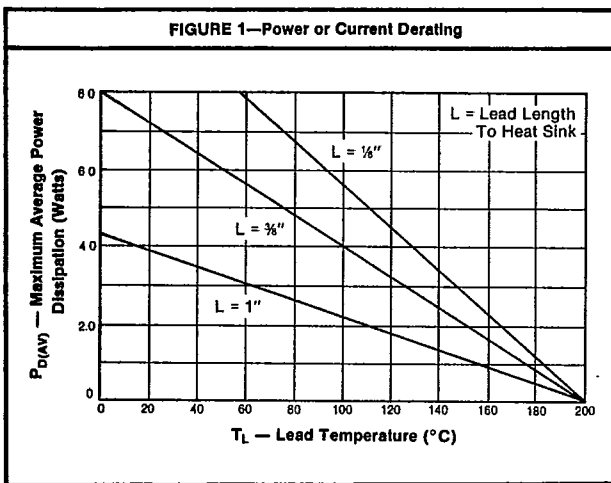
- CASE: Void-free, transfer-molded, thermosetting plastic
- FINISH: All external surfaces are corrosion resistant. Leads are readily solderable
- POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode.
- MOUNTING POSITION: Any
- WEIGHT: 0.7 gram (approximate)

**CASE OUTLINE**



Dimensions (inches): .180" DIA., .165" DIA., .457" DIA., .420" DIA., 1.00" MIN., .335", .315", .852" DIA., .800" DIA., 1.00" MIN., .043" DIA., .037" DIA., 1.092" DIA., .94"

Dimensions (mm): 25.4 MIN. (mm), 8.52 (mm), 8.00 (mm), 25.4 MIN. (mm)



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ELECTRICAL CHARACTERISTICS @ 25°C

JEDEC Type No. (Notes 1 & 2)	Nominal Zener Voltage Vz @ IzT Volts (Note 3)	Test Current IzT mA	Max Zener Impedance A & B Suffix Only		Max Reverse Leakage Current			Applies To All Suffix	A & B Suffix Only	B Suffix Only
			ZzT @ IzT Ohms (Note 3)	Zzk @ Izk = 1.0mA Ohms (Note 3)	In @ Va Volts			Max Surge Current ia, Amps (Note 4)	Max Voltage Regulation ΔVz, Volts (Note 5)	Max Regulator Current IzM mA (Note 6)
					μA	Non & A Suffix	B Suffix			
1N5333	3.3	380	3.0	400	300	1.0	1.0	20.0	0.85	1440
1N5334	3.6	350	2.5	500	150	1.0	1.0	18.7	0.80	1320
1N5335	3.9	320	2.0	500	50	1.0	1.0	17.6	0.54	1220
1N5336	4.3	290	2.0	500	10	1.0	1.0	16.4	0.49	1100
1N5337	4.7	260	2.0	450	5.0	1.0	1.0	15.3	0.44	1010
1N5338	5.1	240	1.5	400	1.0	1.0	1.0	14.4	0.39	930
1N5339	5.6	220	1.0	400	1.0	2.0	2.0	13.4	0.25	865
1N5340	6.0	200	1.0	300	1.0	3.0	3.0	12.7	0.19	790
1N5341	6.2	200	1.0	200	1.0	3.0	3.0	12.4	0.10	765
1N5342	6.8	175	1.0	200	10	4.9	5.2	11.5	0.15	700
1N5343	7.5	175	1.5	200	10	5.4	5.7	10.7	0.15	630
1N5344	8.2	150	1.5	200	10	5.9	6.2	10.0	0.20	590
1N5345	8.7	150	2.0	200	10	6.3	6.6	9.5	0.20	545
1N5346	9.1	150	2.0	150	7.5	6.6	6.9	9.2	0.22	520
1N5347	10	125	2.0	125	5.0	7.2	7.6	8.6	0.22	475
1N5348	11	125	2.5	125	5.0	8.0	8.4	8.0	0.25	430
1N5349	12	100	2.5	125	2.0	8.6	9.1	7.5	0.25	395
1N5350	13	100	2.5	100	1.0	9.4	9.9	7.0	0.25	365
1N5351	14	100	2.5	75	1.0	10.1	10.6	6.7	0.25	340
1N5352	15	75	2.5	75	1.0	10.8	11.5	6.3	0.25	315
1N5353	16	75	2.5	75	1.0	11.5	12.2	6.0	0.30	295
1N5354	17	70	2.5	75	0.5	12.2	12.9	5.8	0.35	280
1N5355	18	65	2.5	75	0.5	13.0	13.7	5.5	0.40	264
1N5356	19	65	3.0	75	0.5	13.7	14.4	5.3	0.40	250
1N5357	20	65	3.0	75	0.5	14.4	15.2	5.1	0.40	237
1N5358	22	50	3.5	75	0.5	15.8	16.7	4.7	0.45	216
1N5359	24	50	3.5	100	0.5	17.3	18.2	4.4	0.55	198
1N5360	25	50	4.0	110	0.5	18.0	19.0	4.3	0.55	190
1N5361	27	50	5.0	120	0.5	19.4	20.6	4.1	0.60	176
1N5362	28	50	6.0	130	0.5	20.1	21.2	3.9	0.60	170
1N5363	30	40	8.0	140	0.5	21.6	22.8	3.7	0.60	158
1N5364	33	40	10	150	0.5	23.8	25.1	3.5	0.60	144
1N5365	36	30	11	160	0.5	25.9	27.4	3.3	0.65	132
1N5366	39	30	14	170	0.5	28.1	29.7	3.1	0.65	122
1N5367	43	30	20	190	0.5	31.0	32.7	2.8	0.70	110
1N5368	47	25	25	210	0.5	33.8	35.8	2.7	0.80	100
1N5369	51	25	27	230	0.5	36.7	38.8	2.5	0.90	93.0
1N5370	56	20	35	280	0.5	40.3	42.6	2.3	1.00	86.0
1N5371	60	20	40	350	0.5	43.0	45.5	2.2	1.20	79.0
1N5372	62	20	42	400	0.5	44.6	47.1	2.1	1.35	76.0
1N5373	68	20	44	500	0.5	49.0	51.7	2.0	1.50	70.0
1N5374	75	20	45	620	0.5	54.0	56.0	1.9	1.60	63.0
1N5375	82	15	65	720	0.5	59.0	62.2	1.8	1.80	58.0
1N5376	87	15	75	760	0.5	63.0	66.0	1.7	2.00	54.5
1N5377	91	15	75	760	0.5	65.5	69.2	1.6	2.20	52.5
1N5378	100	12	90	800	0.5	72.0	76.0	1.5	2.50	47.5
1N5379	110	12	125	1000	0.5	79.2	83.6	1.4	2.50	43.0
1N5380	120	10	170	1150	0.5	86.4	91.2	1.3	2.50	39.5
1N5381	130	10	190	1250	0.5	93.6	98.8	1.2	2.50	36.6
1N5382	140	8.0	230	1500	0.5	101	106	1.2	2.50	34.0
1N5383	150	8.0	330	1500	0.5	108	114	1.1	3.00	31.6
1N5384	160	8.0	350	1650	0.5	115	122	1.1	3.00	29.4
1N5385	170	8.0	380	1750	0.5	122	129	1.0	3.00	28.0
1N5386	180	5.0	430	1750	0.5	130	137	1.0	4.00	26.4
1N5387	190	5.0	450	1850	0.5	137	144	0.9	5.00	25.0
1N5388	200	5.0	480	1850	0.5	144	152	0.9	5.00	23.6

Vr = 1.2 Max. at Ir = 1.0A for all types.

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ZENER DIODES

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NOTES TO ELECTRICAL CHARACTERISTICS

**Note 1: Tolerance Designation**

**TOLERANCE DESIGNATION**—The JEDEC type numbers shown have a tolerance of  $\pm 20\%$  with guaranteed limits on only  $V_Z$ ,  $I_R$ ,  $I_S$  and  $V_F$ . Units with guaranteed limits on all parameters are indicated by suffix "A" for  $\pm 10\%$  tolerance and suffix "B" for  $\pm 5.0\%$  units.

**Note 2: Specials**

Nominal zener voltages between the voltages shown and tighter voltage tolerances can be provided. Consult factory.

**Note 3: Zener Voltage ( $V_Z$ ) and Impedance ( $Z_{ZT}$  &  $Z_{ZK}$ )**

Test conditions for zener voltage and impedance are as follows:  $I_Z$  is applied  $40 \pm 10\text{ms}$  prior to reading. Mounting contacts are located  $3/8"$  to  $1/2"$  from the inside edge of mounting clips to the body of the diode. ( $T_A = 25^\circ\text{C}$ , with a tolerance of from  $-2^\circ\text{C}$  to  $+8^\circ\text{C}$ ).

**Note 4: Surge Current ( $I_S$ )**

Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a pulse width (PW) of 8.3 ms. The data given in Figure 2 may be used to find the maximum surge current for a square wave of any pulse width between 1.0ms and 1000ms by plotting the applicable points on logarithmic paper. Examples of this are shown in Figure 3. The mounting contact is located as specified in Note 3. ( $T_A = 25^\circ\text{C}$  with a tolerance of from  $-2^\circ\text{C}$  to  $+8^\circ\text{C}$ ).

**Note 5: Voltage Regulation ( $\Delta V_Z$ )**

Test conditions for voltage regulation are as follows:  $V_Z$  measurements are made at 10% and then at 50% of the  $I_Z$  max value listed in the electrical characteristics table. The test currents are the same for the 5% and 10% tolerance devices. The test current time duration for each  $V_Z$  measurement is  $40 \pm 10\text{ms}$ . ( $T_A = 25^\circ\text{C}$  with a tolerance of from  $-2^\circ\text{C}$  to  $+8^\circ\text{C}$ ). Mounting contact is located as specified in Note 3.

**Note 6: Maximum Regulator Current ( $I_{ZM}$ )**

The maximum current shown is based on the maximum voltage of a 5% type unit, therefore, it applies exclusively to the "B" suffix device. The actual  $I_{ZM}$  for any device may not exceed the value of 5.0 watts divided by the actual  $V_Z$  of the device. ( $T_L = 75^\circ\text{C}$  at  $3/8"$  maximum from the device body.)

MAXIMUM NON-REPETITIVE SURGE CURRENT

FIGURE 2—Effect of Nominal Zener Voltage for Selected Pulse Widths (Note 4)

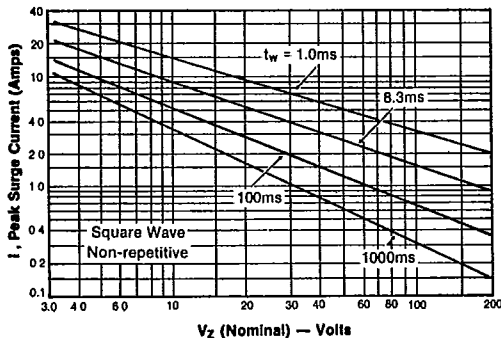
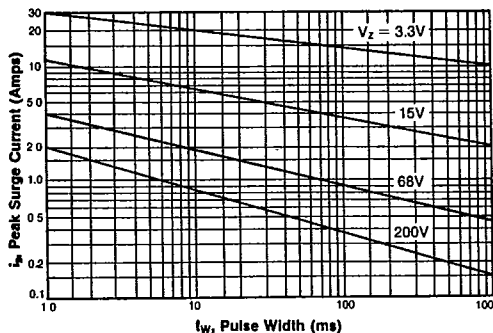


FIGURE 3—Effect of Pulse Width for Selected Zener Voltages



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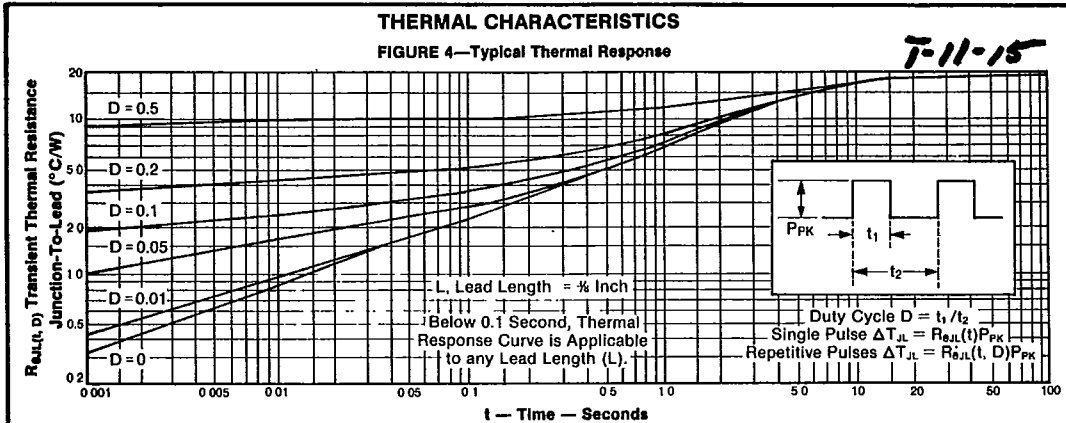


FIGURE 5—Temperature Coefficient Range for Units 3.0 to 10 Volts

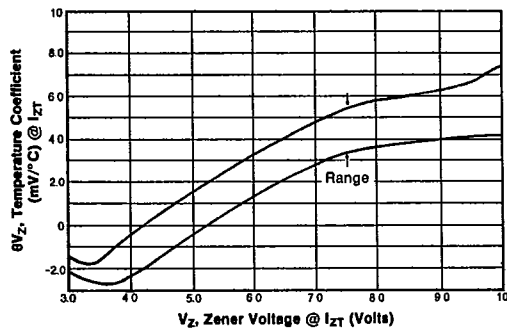


FIGURE 6—Temperature Coefficient Range for Units 10 to 220 Volts

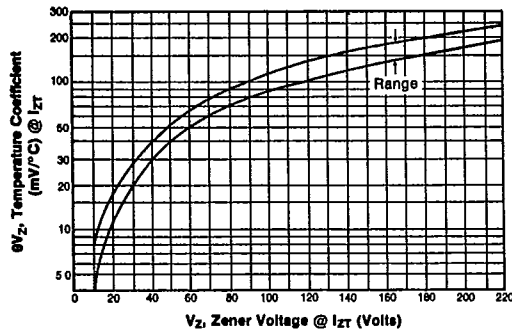
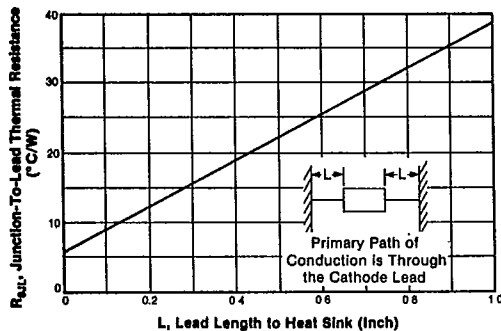


FIGURE 7—Typical Thermal Resistance



**APPLICATION NOTE**

The thermal data should not be used to compute surge capability. The surge limitations given in Figure 1 are lower than would be expected by considering only thermal resistance and rated junction temperature. Current crowding effects cause high hot spot temperatures resulting in device degradation.

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions, in order to calculate its value. The following is recommended:

Lead Temperature ( $T_L$ ) should be determined from:

$$T_L = R_{\theta LA} P_D + T_A$$

$R_{\theta LA}$  is the lead-to-ambient thermal resistance and  $P_D$  is the average power dissipation.  $R_{\theta LA}$  is often difficult to obtain so that a measurement of  $T_L$  is usually preferred.

Junction Temperature ( $T_J$ ) may be found from:

$$T_J = T_L + \Delta T_{JL}$$

$\Delta T_{JL}$  is the increase in junction temperature above the lead temperature. It may be found by using the data of Figure 4 for a train of power pulses or from Figure 7 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of  $I_Z$ , limits of  $P_D$  and the extremes of  $T_J(\Delta T_J)$  may be estimated. The change in voltage over the temperature range can be found from:

$$\Delta V = \theta_{VZ} \Delta T_J$$

$\theta_{VZ}$ , the zener voltage temperature coefficient, is found from Figures 5 and 6.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

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